

HRF22

Silicon Schottky Barrier Diode for High Frequency Rectifying

HITACHI

 Rev. 3
 Feb. 1996

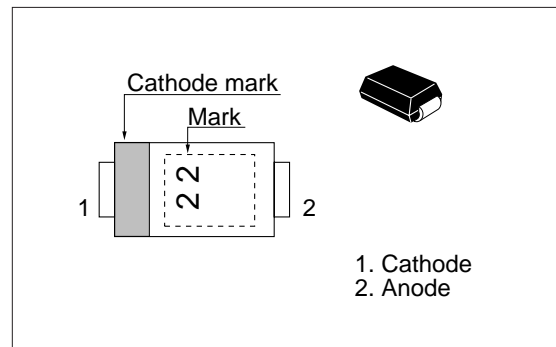
Features

- Good for high-frequency rectify for $V_R=40V$, $I_o=1.0A$, Output voltage=6Vmax.
- LRP structure ensures higher reliability.

Ordering Information

Type No.	Laser Mark	Package Code
HRF22	22	LRP

Outline



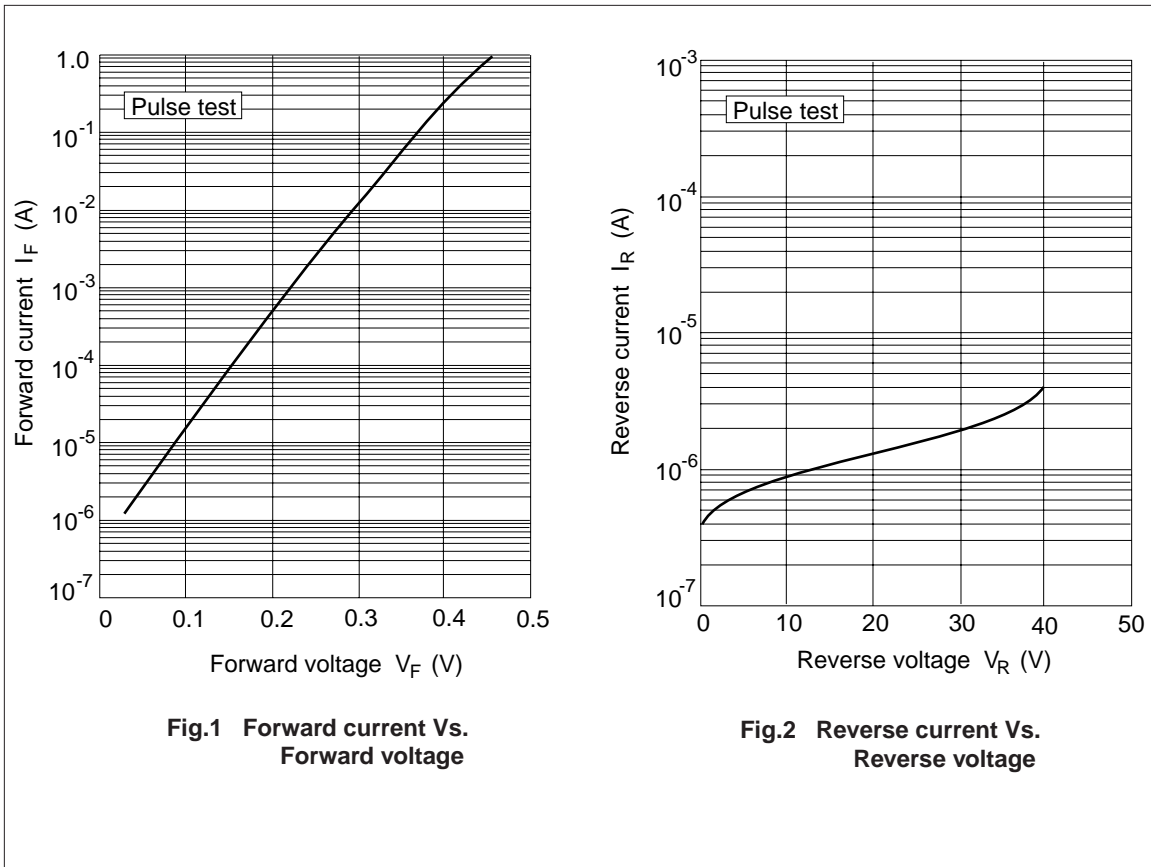
Absolute Maximum Ratings ($T_a = 25^\circ C$)

Item	Symbol	Value	Unit
Repetitive peak reverse voltage	V_{RRM}	40	V
Average forward current	I_o	1.0	A
Non-Repetitive peak forward surge current	I_{FSM}^*	20	A
Junction temperature	T_j	125	$^\circ C$
Storage temperature	T_{stg}	-40 to +125	$^\circ C$

* 10msec sine wave 1 pulse

Electrical Characteristics ($T_a = 25^\circ C$)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V_F	—	—	0.55	V	$I_F = 1.0 A$
Reverse current	I_R	—	—	1.0	mA	$V_R = 40 V$
ESD-Capability	—	150	—	—	V	* $C=200pF$ $R=0\Omega$ Both forward and reversedirection 1 pulse.



Package Dimensions

Unit: mm

